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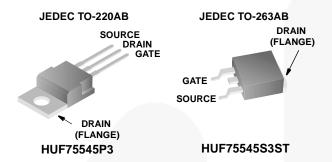
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Data Sheet October 2013

# N-Channel UltraFET Power MOSFET 80 V, 75 A, 10 m $\Omega$

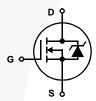
#### **Packaging**



#### **Features**

- Ultra Low On-Resistance
  - $r_{DS(ON)} = 0.010\Omega$ ,  $V_{GS} = 10V$
- · Simulation Models
  - Temperature Compensated PSPICE® and SABER™ Electrical Models
  - Spice and SABER Thermal Impedance Models
  - www.fairchildsemi.com
- · Peak Current vs Pulse Width Curve
- UIS Rating Curve

## Symbol



## Ordering Information

PART NUMBER	PACKAGE	BRAND
HUF75545P3	TO-220AB	75545P
HUF75545S3ST	TO-263AB	75545S

#### **Absolute Maximum Ratings** $T_C = 25^{\circ}C$ , Unless Otherwise Specified

	HUF75545P3, HUF75545S3ST	UNITS
Drain to Source Voltage (Note 1)VDSS	80	V
Drain to Gate Voltage ( $R_{GS} = 20k\Omega$ ) (Note 1)	80	V
Gate to Source Voltage	±20	V
Drain Current		
Continuous (T <sub>C</sub> = 25 <sup>o</sup> C, V <sub>GS</sub> = 10V) (Figure 2)	75	Α
Continuous (T <sub>C</sub> = 100 <sup>o</sup> C, V <sub>GS</sub> = 10V) (Figure 2)	73	Α
Pulsed Drain Current	Figure 4	
Pulsed Avalanche Rating UIS	Figure 6	
Power Dissipation	270	W
Derate Above 25 <sup>o</sup> C	1.8	W/oC
Operating and Storage Temperature	-55 to 175	oC
Maximum Temperature for Soldering		
Leads at 0.063in (1.6mm) from Case for 10s	300	°С
Package Body for 10s, See Techbrief TB334T <sub>pkg</sub>	260	οС
NOTES:		

<sup>1.</sup>  $T_J = 25^{\circ}C$  to  $150^{\circ}C$ .

**CAUTION:** Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

Product reliability information can be found at http://www.fairchildsemi.com/products/discrete/reliability/index.html
For severe environments, see our Automotive HUFA series.

All Fairchild semiconductor products are manufactured, assembled and tested under ISO9000 and QS9000 quality systems certification.

## HUF75545P3, HUF75545S3S

## **Electrical Specifications** $T_C = 25^{\circ}C$ , Unless Otherwise Specified

PARAMETER	SYMBOL	TEST CONDITIONS		MIN	TYP	MAX	UNITS
OFF STATE SPECIFICATIONS							
Drain to Source Breakdown Voltage	BV <sub>DSS</sub>	$I_D = 250\mu A, V_{GS} = 0V \text{ (Figure 11)}$		80	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = 75V, V_{GS} = 0$	V	-	-	1	μА
		V <sub>DS</sub> = 70V, V <sub>GS</sub> = 0	V, T <sub>C</sub> = 150 <sup>o</sup> C	-	-	250	μΑ
Gate to Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V		-	-	±100	nA
ON STATE SPECIFICATIONS	1			1	1		
Gate to Source Threshold Voltage	V <sub>GS(TH)</sub>	$V_{GS} = V_{DS}, I_D = 250$	μΑ (Figure 10)	2	-	4	V
Drain to Source On Resistance	r <sub>DS(ON)</sub>	I <sub>D</sub> = 75A, V <sub>GS</sub> = 10V	(Figure 9)	-	0.0082	0.010	Ω
THERMAL SPECIFICATIONS						I.	1
Thermal Resistance Junction to Case	$R_{\theta JC}$	TO-220 and TO-263 -		-	-	0.55	oC/W
Thermal Resistance Junction to Ambient	$R_{\theta JA}$			-	62	oC/W	
SWITCHING SPECIFICATIONS (VGS	= 10V)			1	1		
Turn-On Time	ton	V <sub>DD</sub> = 40V, I <sub>D</sub> = 75A	-	-	210	ns	
Turn-On Delay Time	t <sub>d</sub> (ON)	$V_{GS} = 10V$ , $R_{GS} = 2.5\Omega$	-	14	-	ns	
Rise Time	t <sub>r</sub>			-	125	-	ns
Turn-Off Delay Time	t <sub>d(OFF)</sub>			-	40	-	ns
Fall Time	t <sub>f</sub>			-	90	-	ns
Turn-Off Time	t <sub>OFF</sub>			-	-	195	ns
GATE CHARGE SPECIFICATIONS	1				1		
Total Gate Charge	Q <sub>g(TOT)</sub>	V <sub>GS</sub> = 0V to 20V	V <sub>DD</sub> = 40V,	-	195	235	nC
Gate Charge at 10V	Q <sub>g(10)</sub>	$V_{GS} = 0V \text{ to } 10V$ $V_{GS} = 0V \text{ to } 2V$ $I_{D} = 75A,$ $I_{g(REF)} = 1.0\text{mA}$ (Figure 13)		-	105	125	nC
Threshold Gate Charge	Q <sub>g(TH)</sub>			-	6.8	8.2	nC
Gate to Source Gate Charge	Q <sub>gs</sub>			-	15	· -	nC
Gate to Drain "Miller" Charge	Q <sub>gd</sub>			-	43	-	nC
CAPACITANCE SPECIFICATIONS				,			
Input Capacitance	C <sub>ISS</sub>	$V_{DS} = 25V, V_{GS} = 0V,$ - 3750 f = 1MHz (Figure 12) - 1100		-	3750	-	pF
Output Capacitance	C <sub>OSS</sub>			-	pF		
Reverse Transfer Capacitance	C <sub>RSS</sub>			-	350	_	pF

## **Source to Drain Diode Specifications**

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Source to Drain Diode Voltage	V <sub>SD</sub>	I <sub>SD</sub> = 75A		-	1.25	V
		I <sub>SD</sub> = 35A	-	-	1.00	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>SD</sub> = 75A, dI <sub>SD</sub> /dt = 100A/μs	-	-	100	ns
Reverse Recovered Charge	Q <sub>RR</sub>	$I_{SD} = 75A$ , $dI_{SD}/dt = 100A/\mu s$	·	-	300	nC

## **Typical Performance Curves**

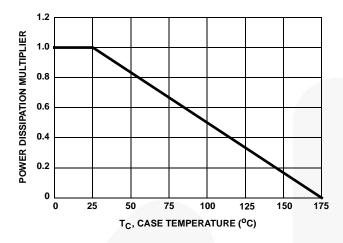


FIGURE 1. NORMALIZED POWER DISSIPATION vs CASE TEMPERATURE

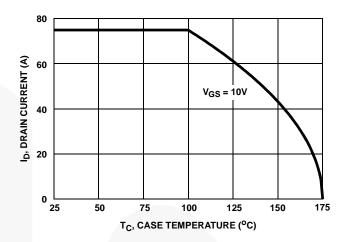


FIGURE 2. MAXIMUM CONTINUOUS DRAIN CURRENT vs CASE TEMPERATURE

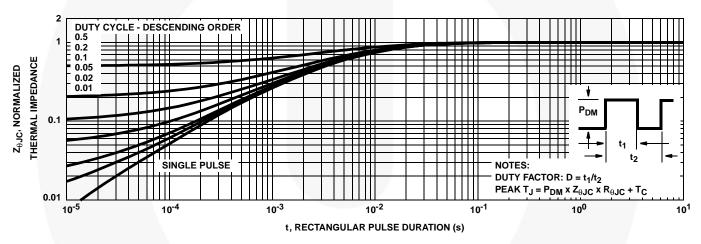


FIGURE 3. NORMALIZED MAXIMUM TRANSIENT THERMAL IMPEDANCE

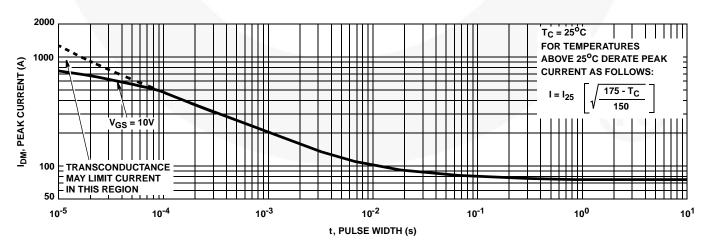


FIGURE 4. PEAK CURRENT CAPABILITY

## Typical Performance Curves (Continued)

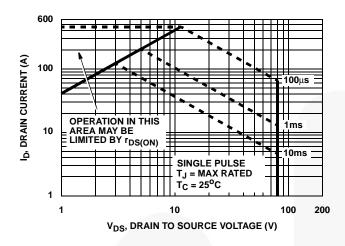


FIGURE 5. FORWARD BIAS SAFE OPERATING AREA

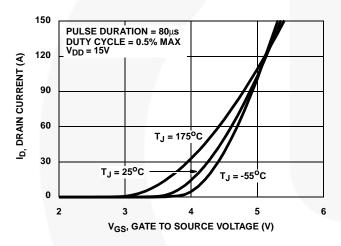


FIGURE 7. TRANSFER CHARACTERISTICS

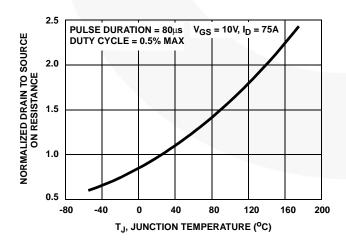
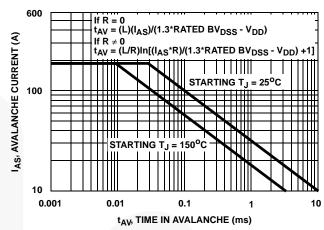


FIGURE 9. NORMALIZED DRAIN TO SOURCE ON RESISTANCE vs JUNCTION TEMPERATURE



NOTE: Refer to Fairchild Application Notes AN9321 and AN9322.

FIGURE 6. UNCLAMPED INDUCTIVE SWITCHING CAPABILITY

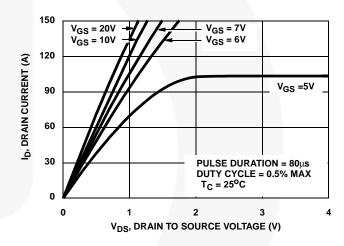


FIGURE 8. SATURATION CHARACTERISTICS

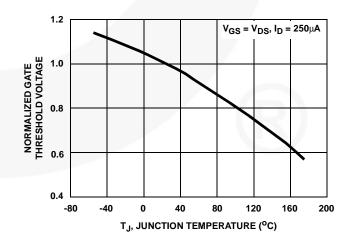
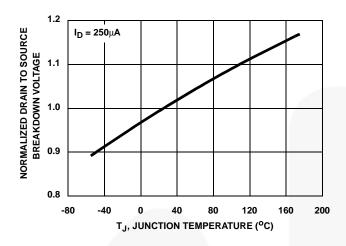


FIGURE 10. NORMALIZED GATE THRESHOLD VOLTAGE vs JUNCTION TEMPERATURE

## Typical Performance Curves (Continued)



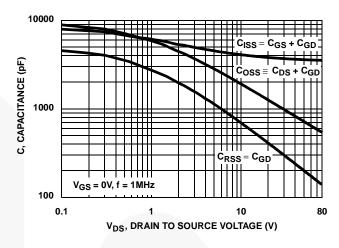
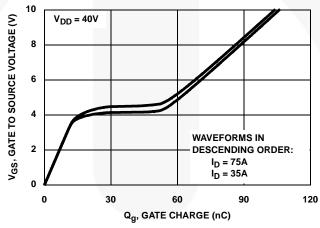


FIGURE 11. NORMALIZED DRAIN TO SOURCE BREAKDOWN VOLTAGE vs JUNCTION TEMPERATURE

FIGURE 12. CAPACITANCE vs DRAIN TO SOURCE VOLTAGE



NOTE: Refer to Fairchild Application Notes AN7254 and AN7260.

FIGURE 13. GATE CHARGE WAVEFORMS FOR CONSTANT GATE CURRENT

## Test Circuits and Waveforms

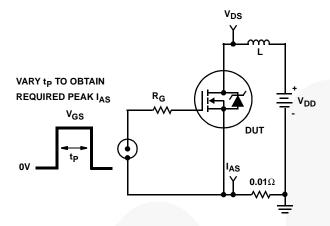


FIGURE 14. UNCLAMPED ENERGY TEST CIRCUIT

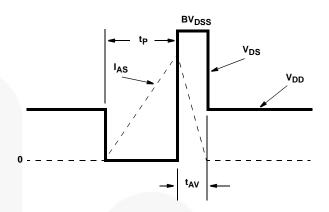


FIGURE 15. UNCLAMPED ENERGY WAVEFORMS

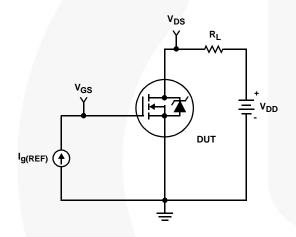


FIGURE 16. GATE CHARGE TEST CIRCUIT

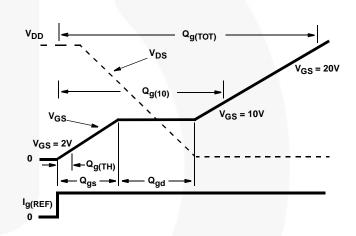


FIGURE 17. GATE CHARGE WAVEFORMS

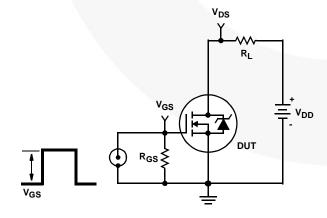


FIGURE 18. SWITCHING TIME TEST CIRCUIT

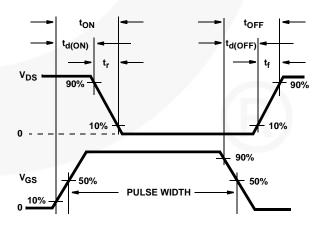
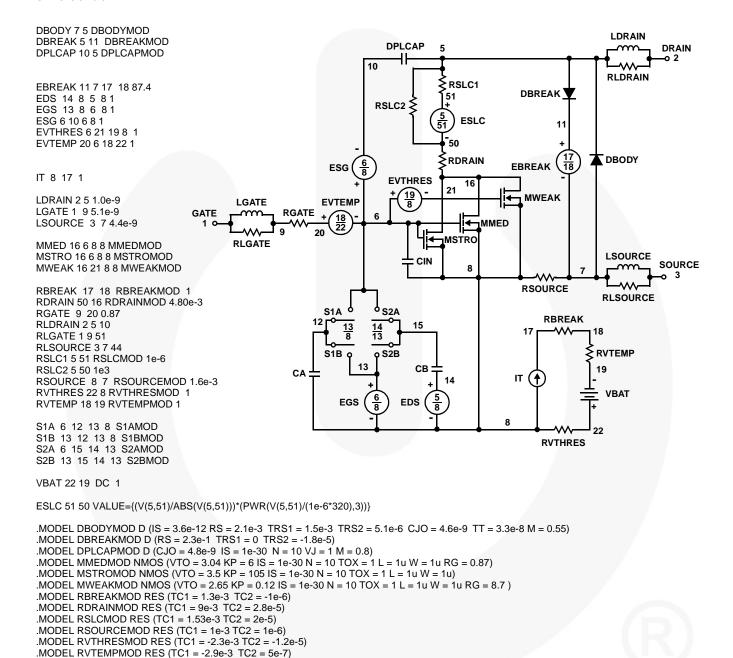


FIGURE 19. SWITCHING TIME WAVEFORM

#### **PSPICE Electrical Model**

.SUBCKT HUF75545 2 1 3; rev 21 May 1999

CA 12 8 5.4e-9 CB 15 14 5.3e-9 CIN 6 8 3.4e-9



.ENDS

NOTE: For further discussion of the PSPICE model, consult **A New PSPICE Sub-Circuit for the Power MOSFET Featuring Global Temperature Options**; IEEE Power Electronics Specialist Conference Records, 1991, written by William J. Hepp and C. Frank Wheatley.

.MODEL S1AMOD VSWITCH (RON = 1e-5 ROFF = 0.1 VON = -5 VOFF= -3)
.MODEL S1BMOD VSWITCH (RON = 1e-5 ROFF = 0.1 VON = -3 VOFF= -5)
.MODEL S2AMOD VSWITCH (RON = 1e-5 ROFF = 0.1 VON = -1.5 VOFF= 0.5)
.MODEL S2BMOD VSWITCH (RON = 1e-5 ROFF = 0.1 VON = 0.5 VOFF= -1.5)

#### SABER Electrical Model

REV 21 may 1999

```
template huf75545 n2,n1,n3
electrical n2,n1,n3
var i iscl
d..model dbodymod = (is = 3.6e-12, cjo = 4.6e-9, tt = 3.3e-8, m = 0.55)
d..model dbreakmod = ()
d..model dplcapmod = (cjo = 4.8e-9, is = 1e-30, vj=1.0, m = 0.8)
m..model mmedmod = (type=_n, vto = 3.04, kp = 6, is = 1e-30, tox = 1)
m..model mstrongmod = (type=_n, vto = 3.5, kp = 105, is = 1e-30, tox = 1)
m..model mweakmod = (type=_n, vto = 2.65, kp = 0.12, is = 1e-30, tox = 1)
                                                                                                                               LDRAIN
                                                                                  DPLCAP
sw_vcsp..model s1amod = (ron = 1e-5, roff = 0.1, von = -5, voff = -3)
                                                                                             5
                                                                                                                                          DRAIN
sw_vcsp..model s1bmod = (ron = 1e-5, roff = 0.1, von = -3, voff = -5)
sw_vcsp..model s2amod = (ron = 1e-5, roff = 0.1, von = -1.5, voff = 0.5)
                                                                                                                               RLDRAIN
sw_vcsp..model s2bmod = (ron = 1e-5, roff = 0.1, von = 0.5, voff = -1.5)
                                                                                              RSLC1
                                                                                                           RDBREAK
                                                                                              51
                                                                               RSLC2
c.ca n12 n8 = 5.4e-9
                                                                                                                   72
                                                                                                                               RDBODY
c.cb n15 n14 = 5.3e-9
                                                                                                 ISCL
c.cin n6 n8 = 3.4e-9
                                                                                                            DBREAK
                                                                                               50
d.dbody n7 n71 = model=dbodymod
                                                                                                                              71
                                                                                              RDRAIN
                                                                            <u>6</u>
8
d.dbreak n72 n11 = model=dbreakmod
                                                                      ESG (
                                                                                                                     11
d.dplcap n10 n5 = model=dplcapmod
                                                                                  EVTHRES
                                                                                              21
                                                                                     (\frac{19}{8})
                                                                                                              MWEAK
                                                                    EVTEMP
                                                   LGATE
i.it n8 n17 = 1
                                                                                                                            ▲ DBODY
                                                            RGATE
                                          GATE
                                                                                                               EBREAK
                                                                                                     MMED
I.ldrain n2 n5 = 1e-9
                                                                   20
I.lgate n1 n9 = 5.1e-9
                                                                                             MSTRO
                                                  RLGATE
I.Isource n3 n7 = 4.4e-9
                                                                                                                               LSOURCE
                                                                                        CIN
                                                                                                                                          SOURCE
                                                                                                  8
m.mmed n16 n6 n8 n8 = model=mmedmod, l=1u, w=1u
m.mstrong n16 n6 n8 n8 = model=mstrongmod, l=1u, w=1u
                                                                                                             RSOURCE
m.mweak n16 n21 n8 n8 = model=mweakmod, l=1u, w=1u
                                                                                                                              RLSOURCE
                                                                                                                  RBREAK
res.rbreak n17 n18 = 1, tc1 = 1.3e-3, tc2 = -1e-6
                                                                                                              17
res.rdbody n71 n5 = 2.1e-3, tc1 = 1.5e-3, tc2 = 5.1e-6
res.rdbreak n72 n5 = 2.3e-1, tc1 = 0, tc2 = -1.8e-5
                                                                                                                             RVTEMP
res.rdrain n50 n16 = 4.8e-3, tc1 = 9e-3, tc2 = 2.8e-5
                                                                                        СВ
                                                                                                                             19
res.rgate n9 n20 = 0.87
                                                              CA
                                                                                                            и (
res.rldrain n2 n5 = 10
res.rlgate n1 n9 = 51
                                                                                                                               VBAT
                                                                        EGS
                                                                                     EDS
res.rlsource n3 n7 = 44
res.rslc1 n5 n51 = 1e-6, tc1 = 1.53e-3, tc2 = 2e-5
                                                                                                          8
res.rslc2 n5 n50 = 1e3
res.rsource n8 n7 = 1.6e-3, tc1 = 1e-3, tc2 = 1e-6
                                                                                                                 RVTHRES
res.rvtemp n18 n19 = 1, tc1 = -2.9e-3, tc2 = 5e-7
res.rvthres n22 n8 = 1, tc1 = -2.3e-3, tc2 = -1.2e-5
spe.ebreak n11 n7 n17 n18 = 87.4
spe.eds n14 n8 n5 n8 = 1
spe.egs n13 n8 n6 n8 = 1
spe.esg n6 n10 n6 n8 = 1
spe.evtemp n20 n6 n18 n22 = 1
spe.evthres n6 n21 n19 n8 = 1
sw_vcsp.s1a n6 n12 n13 n8 = model=s1amod
sw vcsp.s1b n13 n12 n13 n8 = model=s1bmod
sw_vcsp.s2a n6 n15 n14 n13 = model=s2amod
sw_vcsp.s2b n13 n15 n14 n13 = model=s2bmod
v.vbat n22 n19 = dc=1
equations {
i (n51->n50) +=iscl
iscl: v(n51,n50) = ((v(n5,n51)/(1e-9+abs(v(n5,n51))))*((abs(v(n5,n51)*1e6/320))** 3))
```

#### SPICE Thermal Model

REV 21 May 1999

HUF75545T

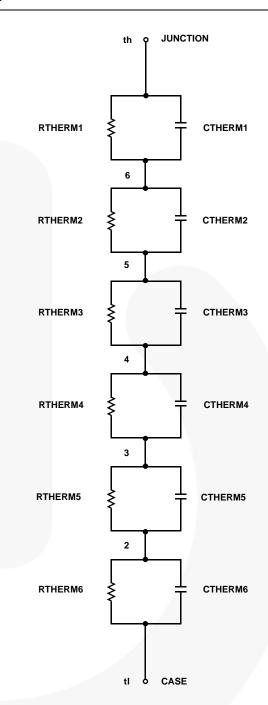
CTHERM1 th 6 6.4e-3 CTHERM2 6 5 3.0e-2 CTHERM3 5 4 1.4e-2 CTHERM4 4 3 1.6e-2 CTHERM5 3 2 5.5e-2 CTHERM6 2 tl 1.5 RTHERM1 th 6 3.2e-3 RTHERM2 6 5 8.1e-3 RTHERM3 5 4 2.3e-2 RTHERM4 4 3 1.3e-1 RTHERM5 3 2 1.8e-1

RTHERM6 2 tl 3.8e-2

## SABER Thermal Model

SABER thermal model HUF75545T

template thermal\_model th tl thermal\_c th, tl  $\{$  ctherm.ctherm1 th 6=6.4e-3 ctherm.ctherm2 6.5=3.0e-2 ctherm.ctherm3 5.4=1.4e-2 ctherm.ctherm4 4.3=1.6e-2 ctherm.ctherm5 3.2=5.5e-2 ctherm.ctherm6 2.tl=1.5 rtherm.rtherm1 th 6=3.2e-3 rtherm.rtherm2 6.5=8.1e-3 rtherm.rtherm3 5.4=2.3e-2 rtherm.rtherm4 5.4=2.3e-2 rtherm.rtherm5 5.2=2.3e-2 rtherm.rtherm6 5.3=2.3e-2 rtherm.rtherm6 5.3=2.3e-2 rtherm.rtherm6 5.3=2.3e-2





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